

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

A technique includes: performing a film formation operation of forming a film containing a metal element on a first surface preferentially over a second surface of a substrate, the act of performing the film formation operation including: (a) forming metal-containing substance containing metal element on at least a portion of the substrate by performing: (a1) supplying a first gas containing the metal element to the substrate including the first surface as a surface of first substance and the second surface as a surface of second substance; and (a2) supplying a second gas containing the metal element to the substrate; and (b) supplying a reaction gas to the substrate, wherein (a) includes a period TC during which (a1) and (a2) are performed simultaneously, wherein the first gas etches the metal-containing substance at a first rate, and wherein the second gas etches the metal-containing substance at a second rate.

Fig. 3